

VUV photodiode

General Features:

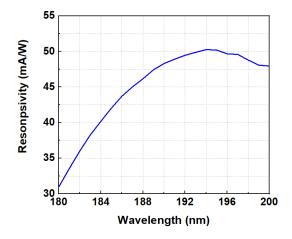
- SiC-based vacuum ultraviolet (VUV) photodiode
- Excellent stability under high fluence VUV exposure
- Photovoltaic mode operation
- Visible blind and low dark current
- High detection efficiency for 193 nm VUV radiation
- Ceramic package

Applications: VUV radiation flux measurement, 193 nm excimer laser monitoring

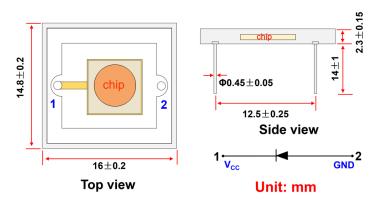


| Parameters | Symbol | Value | Unit |
|---|------------------|--------|------|
| Maximum ratings | | | |
| Operation temperature range | T_{opt} | -20-80 | °C |
| Storage temperature range | T _{sto} | -55-90 | °C |
| Soldering temperature (3 s) | T _{sol} | 260 | °C |
| Maxium reverse voltage | V_{r-max} | -20 | V |
| Electro-Optical characteristics (25 °C) | | | |
| Effective photo-sensitive area | А | 63.5 | mm² |
| Responsivity (@193 nm) | R | 50 | mA/W |
| Dark current (@-1 V) | l _d | < 100 | рА |
| Shunt resistance (@±10 mV) | R _{sh} | > 10 | GΩ |
| Capacitance (@ 0 V and 1 MHz) | Cp | 2.4 | nF |
| Rise time (V_r =0 V , R_L =50 Ω) | t _r | < 2 | μS |

Spectral response



Package dimensions



Model: SCT-VUV64